

CHEMICAL MECHANICAL POLISHING SYSTEM AND PROCESS

Abstract of the Disclosure

Chemical mechanical polishing (CMP) systems and methods are provided
5 herein. One aspect of the present subject matter is a polishing system. One
polishing system embodiment includes a platen adapted to receive a wafer, and a
polishing pad drum that has a cylindrical, or generally cylindrical, shape with a
length and an axis of rotation along the length. The polishing pad drum is adapted
to rotate about the axis of rotation along the drum length. The polishing pad drum,
10 the platen, or both the polishing pad drum and the platen are adapted to be linearly
moved to polish the surface of the wafer using the rotating polishing pad drum. The
polishing pad drum and the platen are adapted to be operably positioned a
predetermined minimum distance from each other as the polishing pad drum and the
platen pass each other due the linear motion.

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